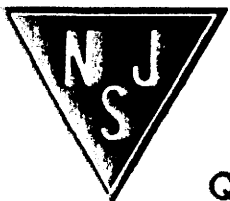
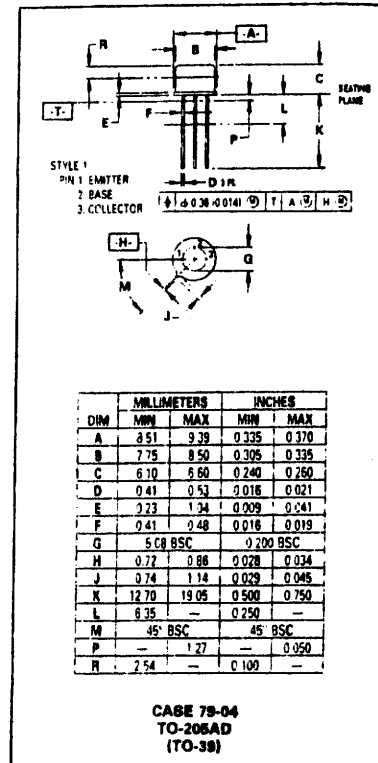


# 2N4271

## SMALL SIGNAL NPN TRANSISTOR

### MAXIMUM RATINGS

Rating	Symbol		Unit
Collector-Emitter Voltage	$V_{CEO}$	1.10	Vdc
Collector-Base Voltage	$V_{CBO}$	1.75	Vdc
Emitter-Base Voltage	$V_{EBO}$	8	Vdc
Base Current	$I_B$	500	Adc
Collector Current — Continuous	$I_C$	1.0	Adc
Continuous Power Dissipation at or Below $T_C = 25^\circ\text{C}$ Linear Derating Factor	$P_D$	5.0 28.6	Watts mW/°C
Continuous Power Dissipation at or Below $T_A = 25^\circ\text{C}$ Linear Derating Factor	$P_D$	1.0 5.72	Watts mW/°C
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200	°C
Lead Temperature 1/16" from Case for 10 Seconds	$T_L$	230	°C



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage ( $I_C = 1.0 \text{ mAdc}$ )	$V_{(BR)CEO}$	140	—	Vdc
Collector Cutoff Current ( $V_{CB} = 30 \text{ Vdc}$ )	$I_{CBO}$	—	50	nAdc
Emitter Cutoff Current ( $V_{EB} = 8 \text{ Vdc}$ )	$I_{EBO}$	—	100	nAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = 0.75 \text{ Adc}$ , $V_{CE} = 10 \text{ Vdc}$ ) ( $I_C = 200 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ ) ( $I_C = .1 \text{ Adc}$ , $V_{CE} = 10 \text{ Vdc}$ )	$h_{FE}$	15 20 10	— 140 —	—
Collector-Emitter Saturation Voltage ( $I_C = .750 \text{ Adc}$ , $I_B = 250 \text{ mAdc}$ )	$V_{CE(sat)}$	—	3	Vdc
Base Emitter Saturation Voltage ( $I_C = 0.5 \text{ mAdc}$ , $V_{CE} = 3.0 \text{ Vdc}$ )	$V_{BE(sat)}$	0.55	.8	Vdc